

Quad 2-Input NAND Gate Logic IC in bare die form

Rev 1.0 21/11/17

Description

The CD4011B is fabricated using a 3µm 15CMOS process. The device has equal source and sink current capabilities and conforms to standard B series output drive. Device outputs are buffered which improves transfer characteristics by providing very high gain. The device is capable of driving x2 low power TTL loads or x1 LSTTL load.

Ordering Information

The following part suffixes apply:

- No suffix MIL-STD-883 /2010B Visual Inspection
- "H" MIL-STD-883 /2010B Visual Inspection+ MIL-PRF-38534 Class H LAT
- "K" MIL-STD-883 /2010A Visual Inspection (Space)
 + MIL-PRF-38534 Class K LAT

LAT = Lot Acceptance Test.

For more information on LAT flows please see below.

www.siliconsupplies.com\quality\bare-die-lot-qualification

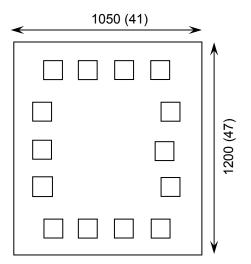
Supply Formats:

- Default Die in Waffle Pack (400 per tray capacity)
- Sawn Wafer on Tape On request
- Unsawn Wafer On request
- Die Thickness <> 350µm(14 Mils) On request
- Assembled into Ceramic Package On request

Features:

- High Input Voltage up to 20V
- Symmetrical Output Characteristics
- Max input current 1µA at 18V over full Military Temperature Range
- Low Power TTL compatible
- Specified at 5V, 10V & 15V
- Direct drop-in replacement for obsolete components in long term programs.

Die Dimensions in µm (mils)



Mechanical Specification

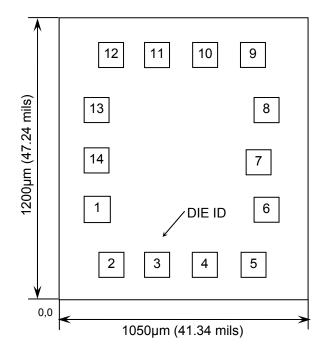
Die Size (Unsawn)	1050 x 1200 41 x 47	μm mils	
Minimum Bond Pad Size	100 x 100 3.94 x 3.94	µm mils	
Die Thickness	350 (±20) 13.78 (±0.79)	µm mils	
Top Metal Composition	Al 1%Si 1.1μm		
Back Metal Composition	N/A – Bare Si		





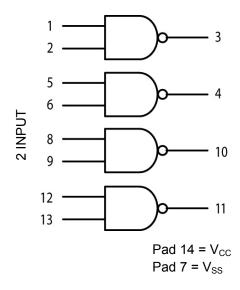
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Pad Layout and Functions



COORDINATES (mm) FUNCTION PAD Χ 1 1A 0.108 0.340 2 2A 0.165 0.108 OUT A 3 0.362 0.108 4 OUT B 0.566 0.108 5 1B 0.763 0.108 2B 0.820 6 0.340 7 0.785 V_{SS} 0.542 1C 0.820 8 0.759 2C 9 0.763 0.991 10 **OUT C** 0.566 0.991 11 OUT D 0.362 0.991 12 1D 0.165 0.991 13 2D 0.108 0.759 14 0.108 V_{DD} 0.548 CONNECT CHIP BACK TO VDD OR FLOAT

Circuit Schematic



Truth Table

INPUTS		OUTPUT			
Α	В	Υ			
L	L	Н			
L	Н	Н			
Н	L	Н			
Н	Н	L			
H = High level (steady state)					
L = Low level (steady state)					





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Absolute Maximum Ratings¹

PARAMETER	SYMBOL	VALUE	UNIT
DC Supply Voltage (Referenced to V _{SS})	V_{DD}	-0.5 to +20	V
DC Input or Output Voltage (Referenced to V _{SS})	$V_{IN,}V_{OUT}$	-0.5 to V _{DD} +0.5	V
Storage Temperature Range	T _{STG}	-65 to 150	°C
Input Current or Output Current (per Pad)	I _{IN} , I _{OUT}	±10	mA
Power Dissipation in Still Air ²	P _D	750	mW

^{1.} Operation above the absolute maximum rating may cause device failure. Operation at the absolute maximum ratings, for extended periods, may reduce device reliability. 2. Measured in plastic DIP package, results in die form are dependent on die attach and assembly method.

Recommended Operating Conditions³ (Voltages referenced to V_{ss})

PARAMETER	SYMBOL	MIN	MAX	UNITS
Supply Voltage	V_{DD}	3.0	18	V
DC Input Voltage, Output Voltage	V _{IN.} V _{OUT}	0	V_{DD}	V
Operating Temperature Range	T _J	-55	+125	°C

^{3.} This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation, V_{IN} and V_{OUT} should be constrained to the range $V_{SS} \le (V_{IN} \text{ or } V_{OUT}) \le V_{DD}$. Unused inputs must always be tied to an appropriate logic voltage level (e.g., either V_{SS} or V_{DD}). Unused outputs must be left open.

DC Electrical Characteristics (Voltages referenced to Vss)

PARAMETER	SYMBOL	V _{DD}	CONDITIONS		UNITS		
			CONDITIONS	25°C	85°C	FULL RANGE⁴	Oitilo
		5V	V _{OUT} = 0.5V	3.5	3.5	3.5	V
Minimum High-Level Input Voltage	V _{IH}	10V	V _{OUT} = 1.0V	7	7	7	
mpat voltago		15V	V _{OUT} = 1.5V	11	11	11	
Maximumalaurlaurl		5V	V _{OUT} = 0.5V	1.5	1.5	1.5	
Maximum Low-Level Input Voltage	V _{IL}	10V	V _{OUT} = 1.0V	3	3	3	V
input voitage		15V	V _{OUT} = 1.5V	4	4	4	
	V _{OH}	5V	V _{IN} = V _{SS}	4.95	4.95	4.95	V
Minimum High-Level Output Voltage		10V		9.95	9.95	9.95	
Output Voltage		15V		14.95	14.95	14.95	
Marrianna I ann I annal	V _{OL} 10\	5V	$V_{IN} = V_{DD}$ or V_{SS}	0.05	0.05	0.05	
Maximum Low-Level Output Voltage		10V		0.05	0.05	0.05	
Catput Voltago		15V		0.05	0.05	0.05	
Maximum Input Leakage Current	I _{IN}	18V	$V_{IN} = V_{DD}$ or V_{SS}	±0.1	±.0.1	±1.0	μA
Maximum Quiescent Supply Leakage Current	I _{CC}	5V	$V_{IN} = V_{DD}$ or V_{SS} $I_{OUT} = 0\mu A$	0.25	0.25	7.5	μА
		10V		0.5	0.5	15	
		15V		1.0	1.0	30	
		20V		5.0	5.0	150	





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DC Electrical Characteristics Continued (Voltages referenced to Vss)

PARAMETER	SYMBOL	V _{DD} CONDITIONS	CONDITIONS		UNITS		
			25°C	85°C	FULL RANGE⁴	Oitilo	
Minimum Output Low (Sink) Current	l _{OL}	5V	$V_{IN} = V_{DD} \text{ or } V_{SS}$ $V_{OL} = 0.4V$	0.64	0.51	0.36	
		10V	$V_{IN} = V_{DD} \text{ or } V_{SS}$ $V_{OL} = 0.5V$	1.6	1.3	0.9	mA
		15V	$V_{IN} = V_{DD} \text{ or } V_{SS}$ $V_{OL} = 1.5V$	4.2	3.4	2.4	
Minimum Output High (Source) Current	I _{OH} 5	5V	$V_{IN} = V_{DD} \text{ or } V_{SS}$ $V_{OH} = 2.5V$	-2.0	-1.6	-1.15	V
		5V	$V_{IN} = V_{DD} \text{ or } V_{SS}$ $V_{OH} = 4.6V$	-0.64	-0.51	-0.36	
		10V	$V_{IN} = V_{DD} \text{ or } V_{SS}$ $V_{OH} = 9.5V$	-1.6	-1.3	-0.9	
		15V	$V_{IN} = V_{DD} \text{ or } V_{SS}$ $V_{OH} = 13.5V$	-4.2	-3.4	-2.4	

⁴. -55°C ≤ T_J ≤ +125°C.

AC Electrical Characteristics⁵

PARAMETER	SYMBOL	V _{DD}	CONDITIONS	TYPICAL		LIMITS	UNITS
		₹ 00	CONDITIONS	25°C	85°C	FULL RANGE⁴	
Propagation Delay,		5V	$C_L = 50pF,$ $R_L = 200k\Omega$ $t_r = t_f = 20ns$	125	250	250	ns
Input A or B to	t _{PLH} , t _{PHL}	10V		60	100	120	
Output Y (Figure 1)		15V		45	80	90	
Output Transition		5V	C_L = 50pF, R_L = 200k Ω t_r = t_f = 20ns	100	250	200	
Time, Any Output	t _{TLH} , t _{THL}	10V		50	100	100	ns
(Figure 1)	1	15V		40	80	80	
Input Capacitance	C _{IN}	-	$C_L = 50 pF,$ $R_L = 200 k\Omega$ $t_r = t_f = 20 ns$	5	7.5	7.5	pF

^{5.} Not production testing in die form, characterized by chip design and tested in package.

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